

MA2S377

Silicon epitaxial planar type

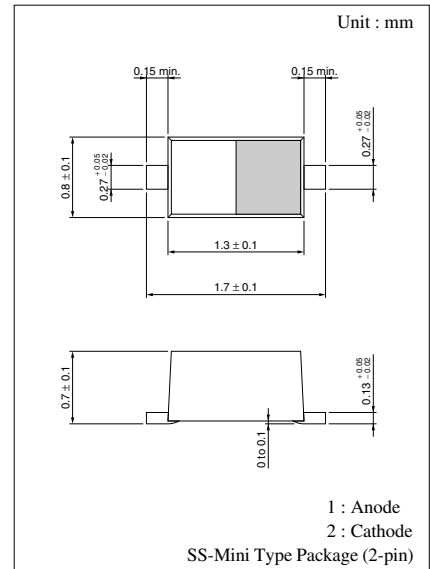
For VCO and TCXO

■ Features

- SS-mini type package, allowing downsizing of equipment and automatic insertion through the taping package

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	12	V
Forward current (DC)	I_F	20	mA
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$



Marking Symbol: 7

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 12\text{ V}$			10	nA
Diode capacitance	$C_{D(2V)}$	$V_R = 2\text{ V}, f = 1\text{ MHz}$	2.80		3.40	pF
	$C_{D(10V)}$	$V_R = 10\text{ V}, f = 1\text{ MHz}$	1.10		1.50	pF
Capacitance ratio	$C_{D(2V)}/C_{D(10V)}$		2.20		2.80	—
Series resistance*	r_D	$V_R = 1\text{ V}, f = 470\text{ MHz}$		0.40	0.60	Ω

Note) 1. Rated input/output frequency: 470 MHz

2. *: r_f measuring instrument: YHP MODEL 4191A RF IMPEDANCE ANALYZER

